

60V NPN DARLINGTON TRANSISTOR IN SOT23
Description

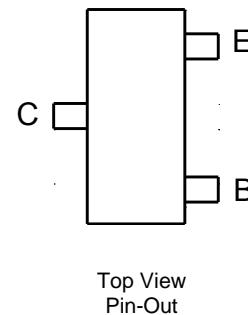
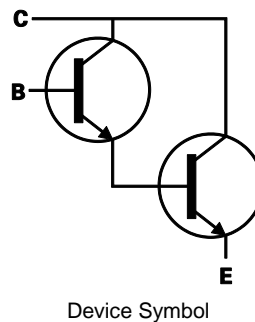
This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- $BV_{CEO} > 60V$
- Darlington Transistor $h_{FE} > 10k$ @ 100mA for High Gain
- $I_C = 500mA$ High Continuous Collector Current
- Complementary Darlington PNP Type: BCV46
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

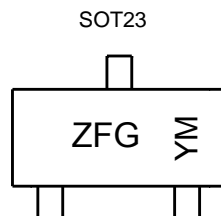
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ③
- Weight 0.008 grams (Approximate)


Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BCV47QTA	Automotive	ZFG	7	8	3,000
BCV47QTC	Automotive	ZFG	13	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
 5. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information


ZFG = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: E = 2017)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	E	F	G	H	I	J	K	L	M	N	O	P

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	10	V
Continuous Collector Current	I _C	500	mA
Peak Pulse Current	I _{CM}	800	mA
Base Current	I _B	100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

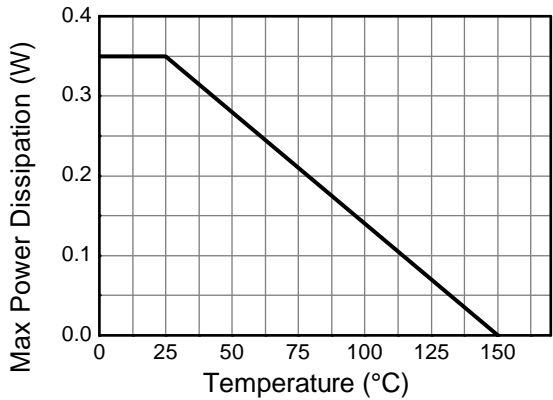
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	(Note 6) 310	mW
		(Note 7) 350	
Thermal Resistance, Junction to Ambient	R _{θJA}	(Note 6) 403	°C/W
		(Note 7) 357	
Thermal Resistance, Junction to Leads	R _{θJL}	350	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

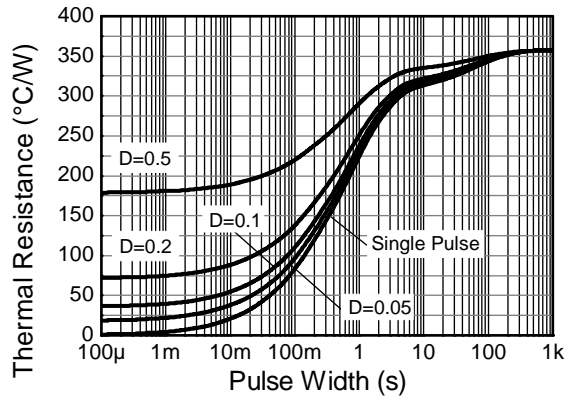
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

- Notes:
6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition; the device is measured when operating in a steady-state condition.
 7. Same as note (6), except the device is mounted on 15mm x 15mm FR4 PCB.
 8. Thermal resistance from junction to solder-point (at the end of the leads).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

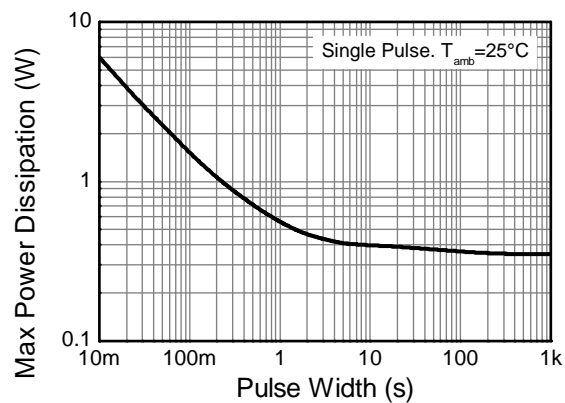
Thermal Characteristics and Derating Information (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Derating Curve



Transient Thermal Impedance



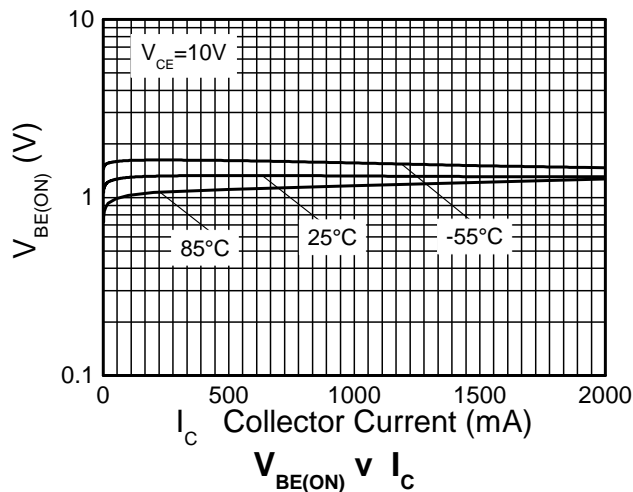
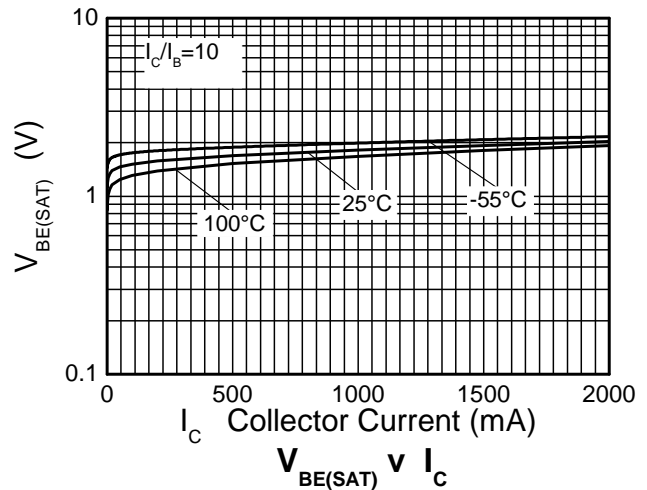
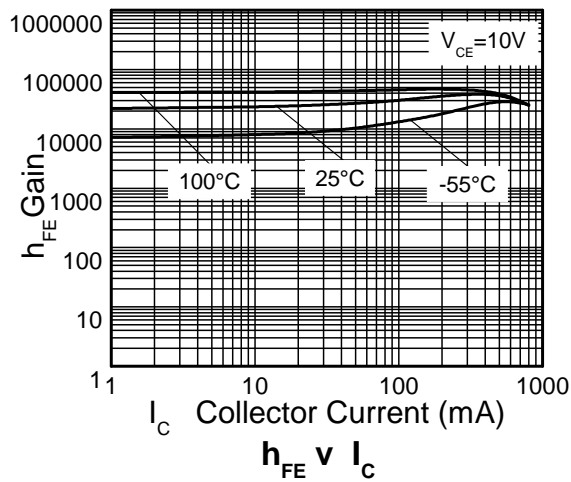
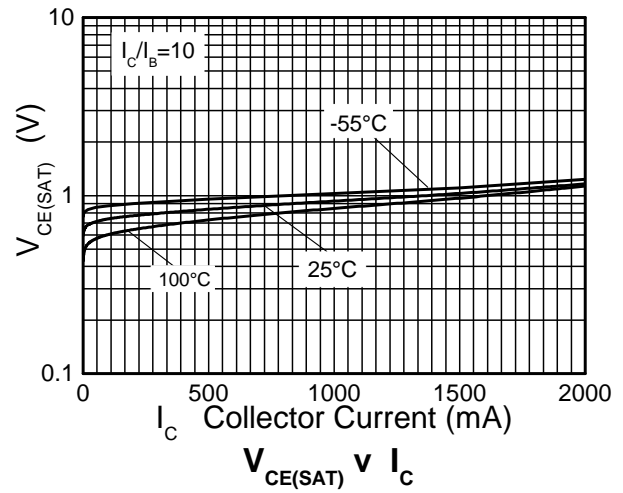
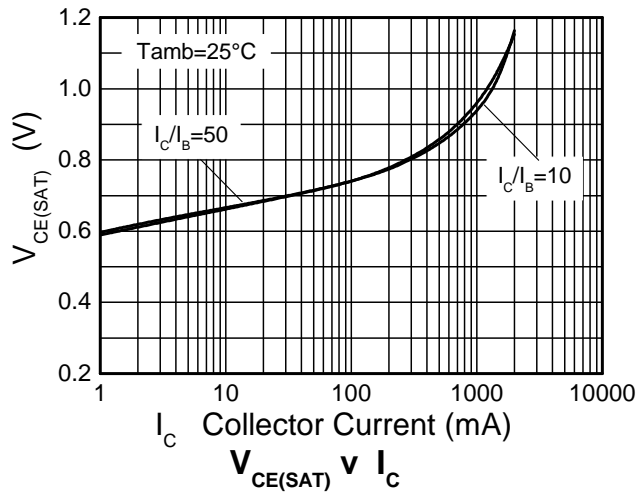
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	80	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	60	—	—	V	I _{CEO} = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	10	—	—	V	I _{EBO} = 10μA
Collector cut-off current	I _{CBO}	—	<1	100	nA	V _{CB} = 60V
		—	—	10	μA	V _{CB} = 60V, T _A = +150°C
Emitter-base Cut-off Current	I _{EBO}	—	<1	100	nA	V _{EB} = 4V
ON CHARACTERISTICS (Note 10)						
Static Forward Current Transfer Ratio	h _{FE}	2,000 4,000 10,000 2,000	—	—	—	I _C = 100μA, V _{CE} = 1V I _C = 10mA, V _{CE} = 5V I _C = 100mA, V _{CE} = 5V I _C = 500mA, V _{CE} = 5V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	—	1.0	V	I _C = 100mA, I _B = 0.1mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	—	1.5	V	I _C = 100mA, I _B = 0.1mA
SMALL SIGNAL CHARACTERISTICS (Note 10)						
Transition Frequency	f _T	—	170	—	MHz	I _C = 50mA, V _{CE} = 5V, f = 20MHz
Output Capacitance	C _{obo}	—	3.5	—	pF	V _{CB} = 10V, f = 1MHz

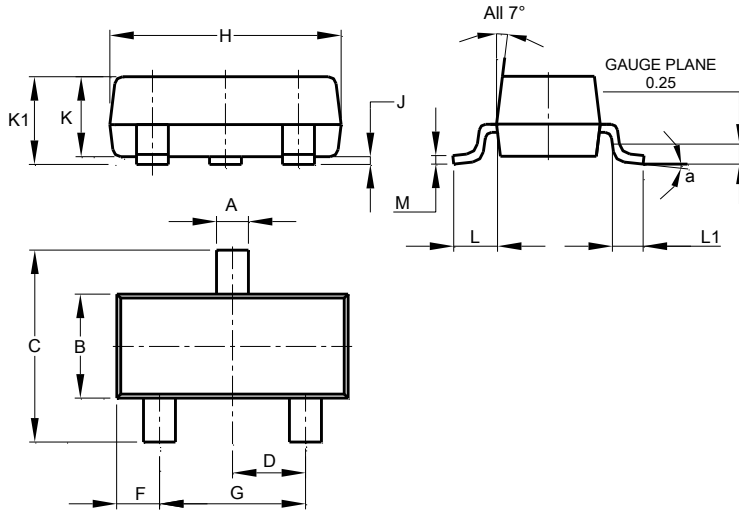
Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



Package Outline Dimensions

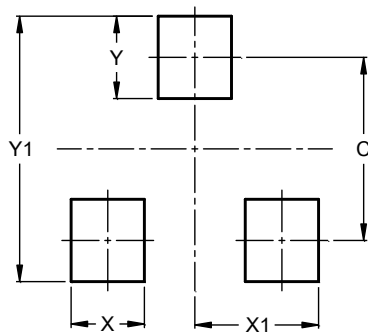
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9